

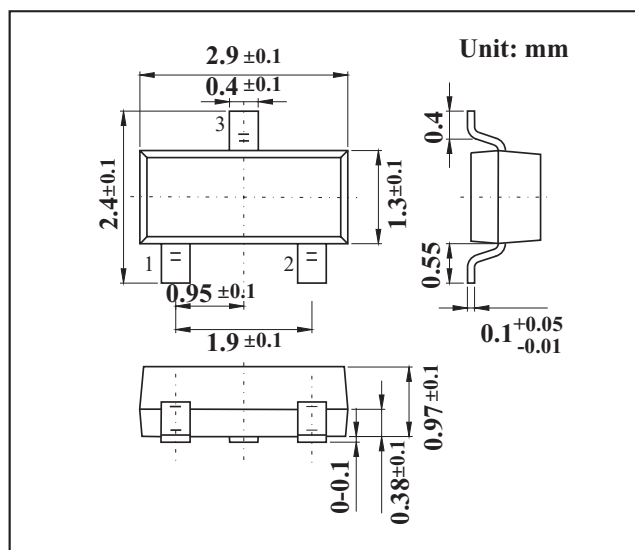
SOT-23 Plastic-Encapsulate Transistors

Features

- Excellent hFE linearity
- Collector Current :IC=0.1A
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current -Continuous	I _C	0.1	A
Collector Power Dissipation	P _C	0.2	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

PACKAGE INFORMATION

Device	Package	Shipping
S9014	SOT-23	3000/Tape&

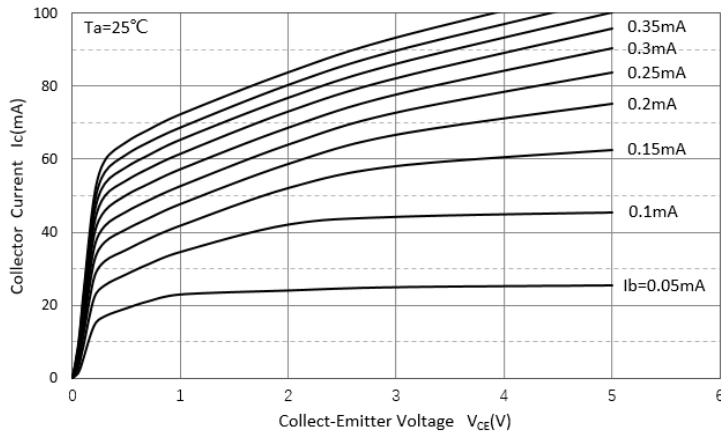
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C =100uA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =1mA, I _B =0	45			V
Emitter-base Breakdown voltage	V _{EB0}	I _E =100 μ A, I _C =0	5			V
Collector cutoff current	I _{CBO}	V _{CB} =50V, I _E =0			0.1	μ A
Emitter cutoff current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μ A
DC current gain	h _{FE}	V _{CE} =5V, I _C =1mA	200		1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA			1	V
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f=30MHZ	150			MHz

hFE Classification

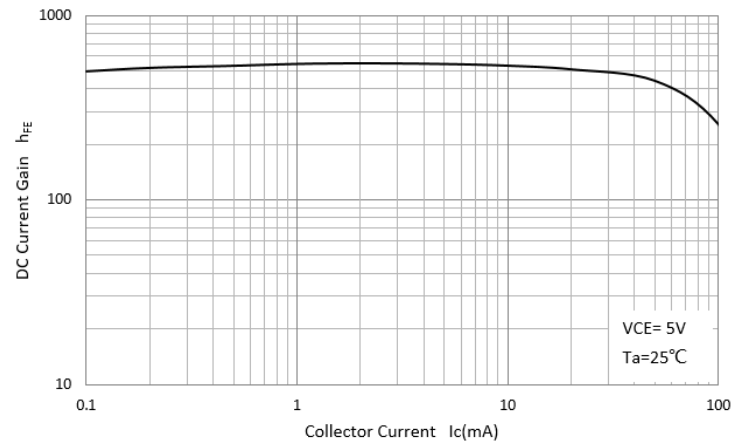
Type	S9014-L	S9014-H
Range	200-450	450-1000
Marking	J6	

RATINGS AND CHARACTERISTIC CURVES

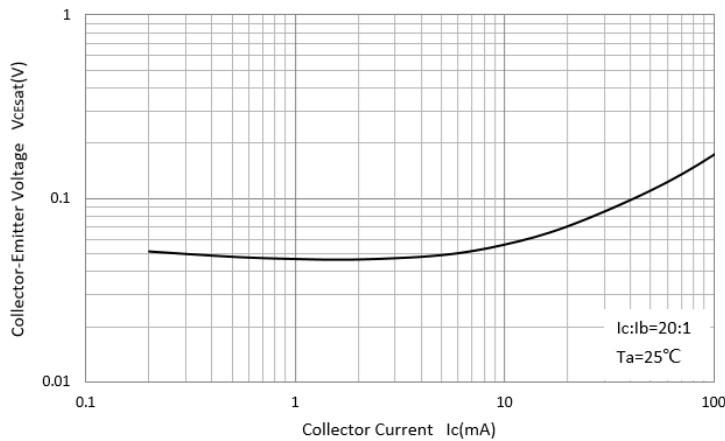
Static Characteristic



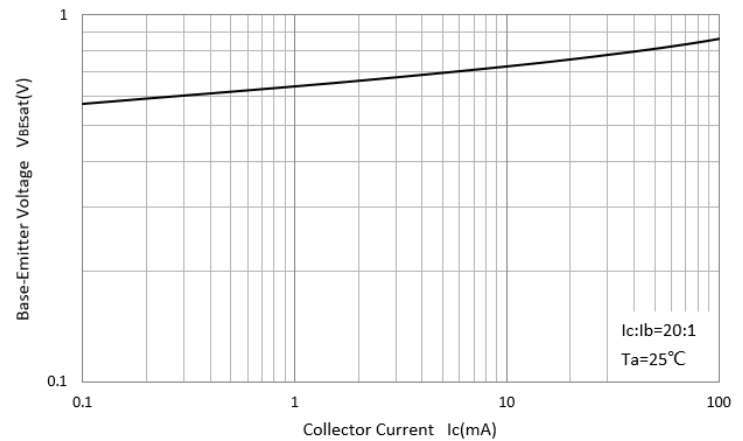
DC Current Gain



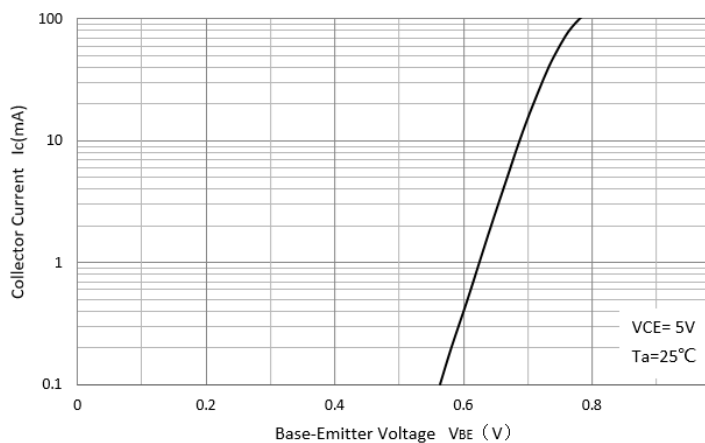
Collector-Emmitter Saturation Voltage



Base-Emmitter Saturation Voltage



Base-Emmitter On Voltage



Capacitance

